

REMARKS

The specification has been amended to correct errors of a typographical and grammatical nature. Due to the number of corrections thereto, applicants submit herewith a Substitute Specification, along with a marked-up copy of the original specification for the Examiner's convenience. The substitute specification includes the changes as shown in the marked-up copy and includes no new matter. Therefore, entry of the Substitute Specification is respectfully requested.

The abstract has also been amended to more clearly describe the features of the present invention.

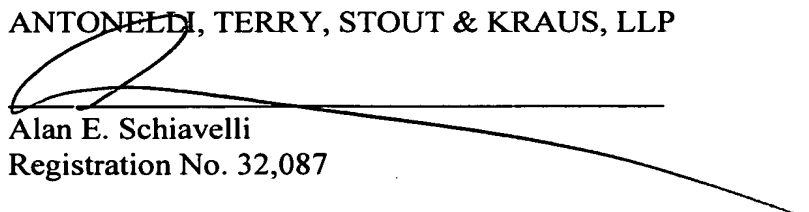
Also submitted herewith is a proposed amendment to the drawings, wherein Figs. 1 - 9 have been amended at this time. Upon receipt of the approval of the amendment to the drawings and receipt of a Notice of Allowance, the proposed drawing corrections will be effected in accordance with present practice.

Entry of the preliminary amendments and examination of the application is respectfully requested.

To the extent necessary, applicant's petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 01-2135 (501.40536X00) and please credit any excess fees to such deposit account.

Respectfully submitted,

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ABSTRACT OF THE DISCLOSURE

~~An object of the present invention is to provide~~ In the manufacture of a semiconductor
device having a high-performance and high-reliability semiconductor device. ~~A~~ a silicon nitride
film 17 for self alignment, which film is formed to cover the gate electrode of a MISFET, is
formed at a substrate temperature of 400°C or greater by plasma CVD using a raw material gas
~~having including~~ including monosilane and nitrogen. A silicon nitride film 44 constituting a passivation
film is formed at a substrate temperature of about 350°C by plasma CVD using a raw material
gas ~~having including~~ including monosilane, ammonia and nitrogen. The hydrogen content contained in the
silicon nitride film 17 is smaller than that contained in the silicon nitride film 44, making it
possible to suppress hydrogen release from the silicon nitride film 17.

FIG. 1(a)

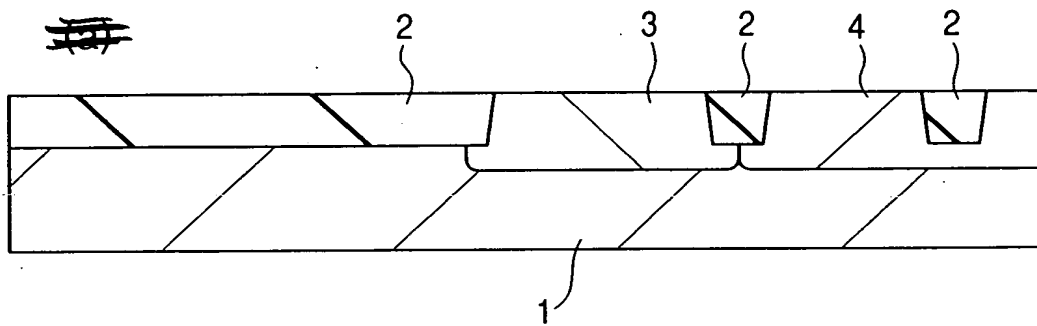


FIG. 1(b)

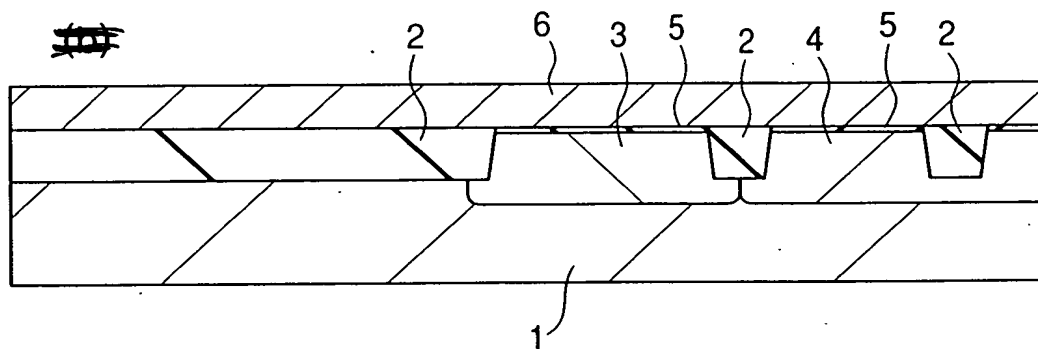


FIG. 1(c)

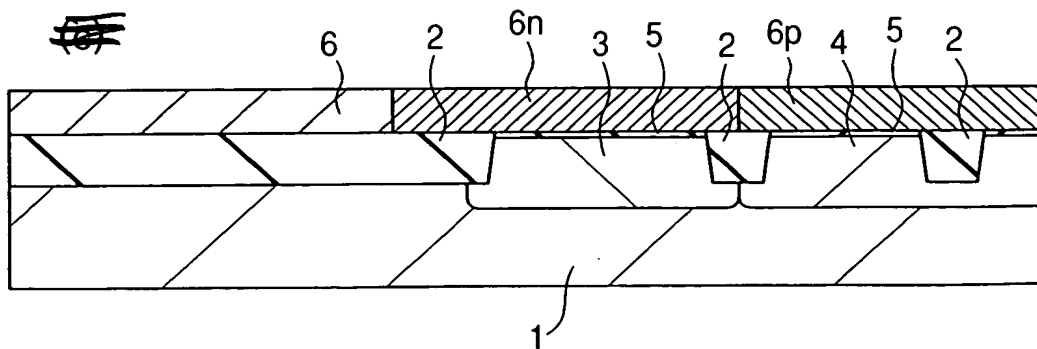


FIG. 2(a)

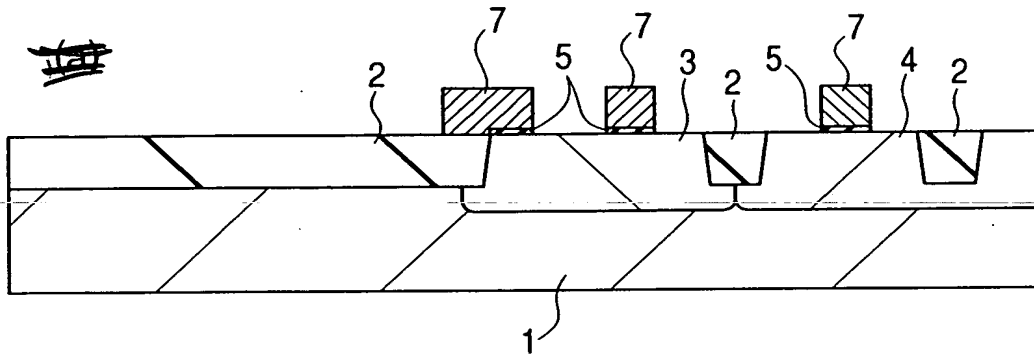


FIG. 2(b)

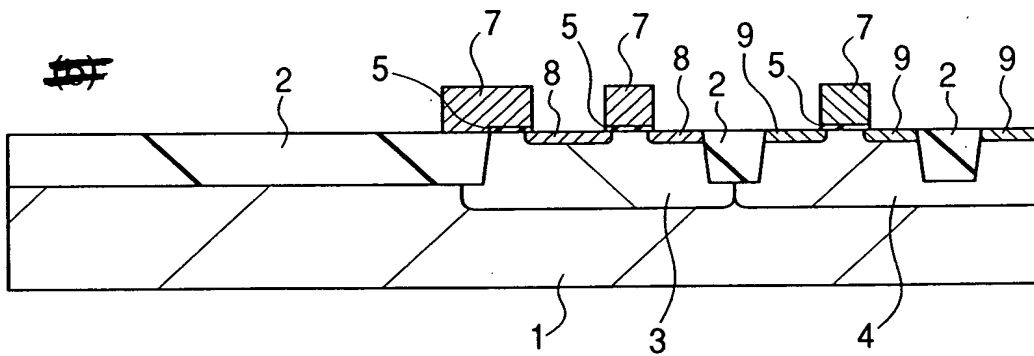


FIG. 2(c)

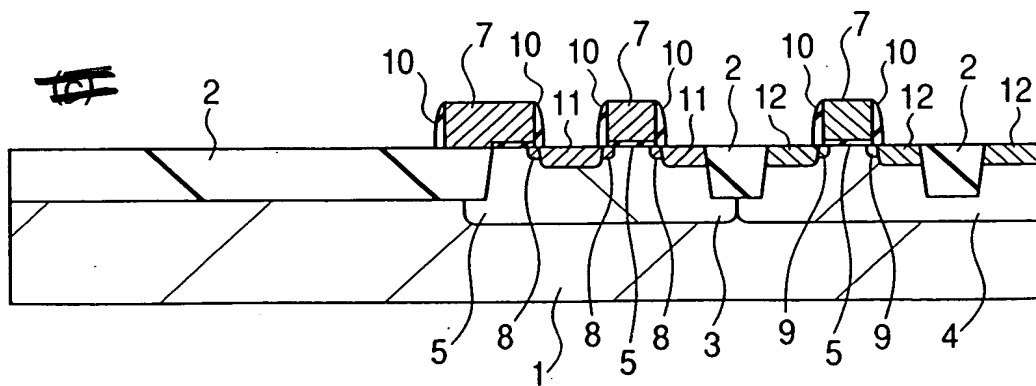


FIG. 3(a)

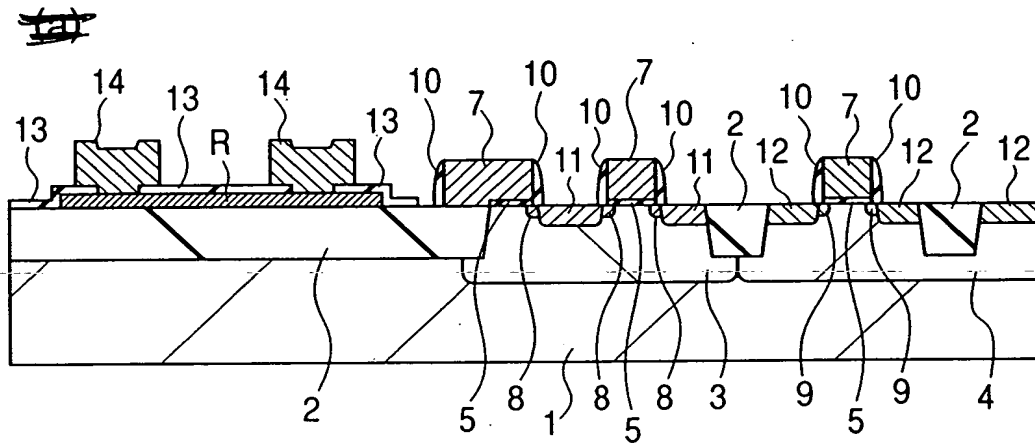


FIG. 3(b)

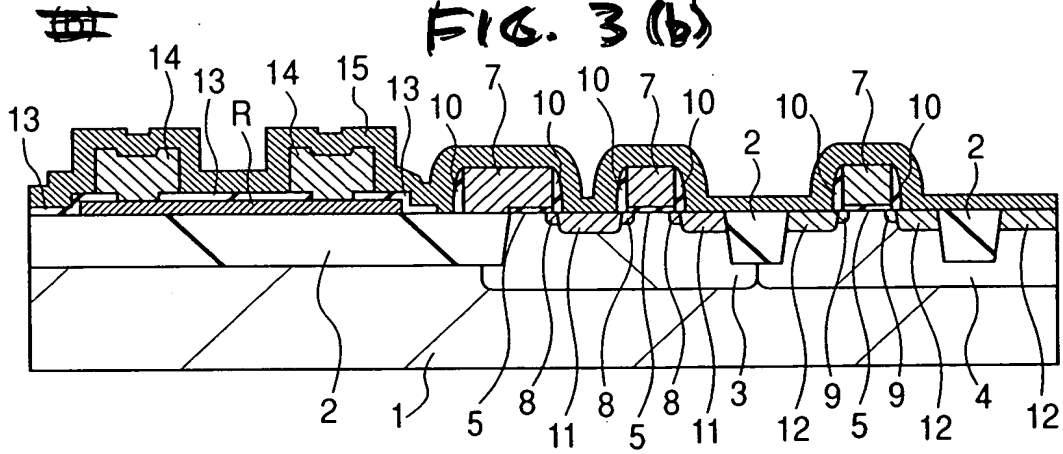


FIG. 3(c)

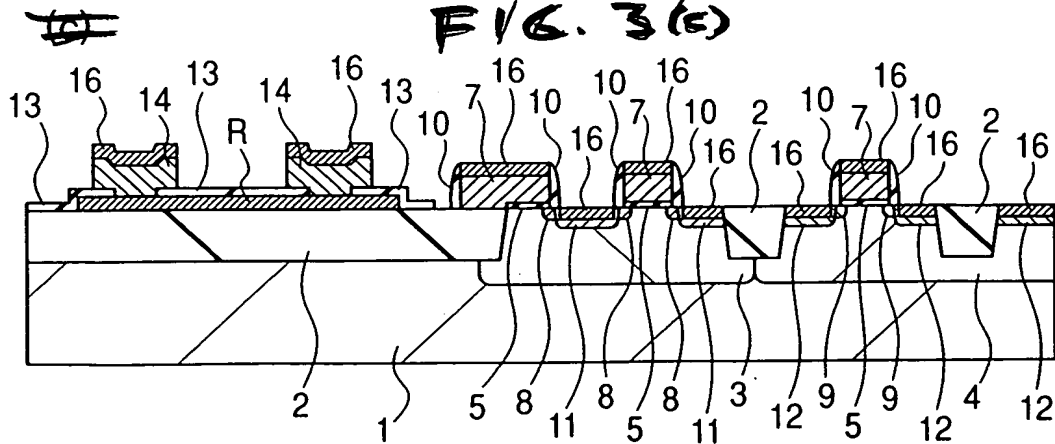


FIG. 4(a)

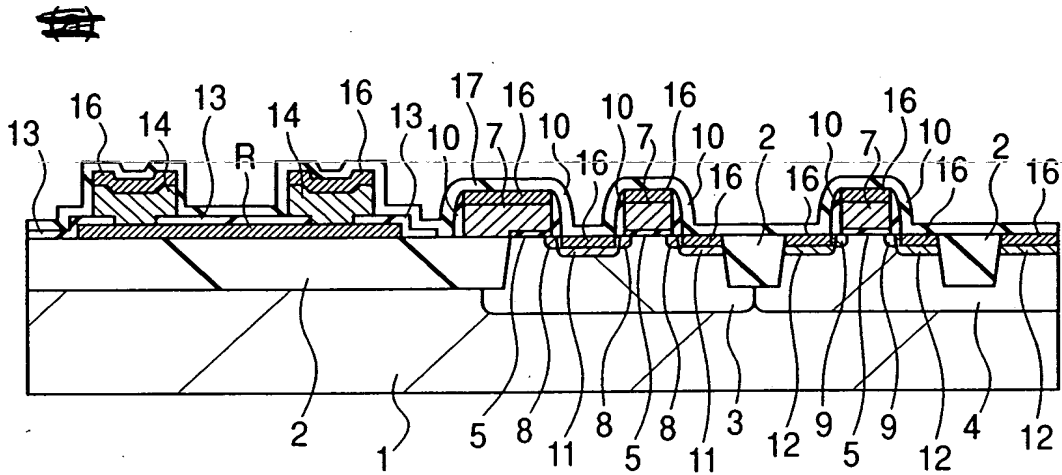
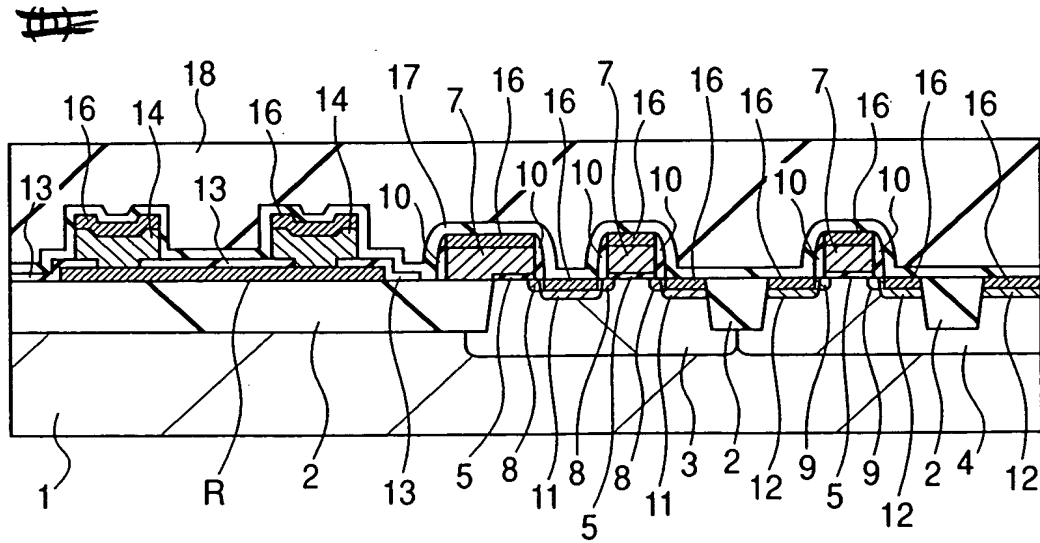
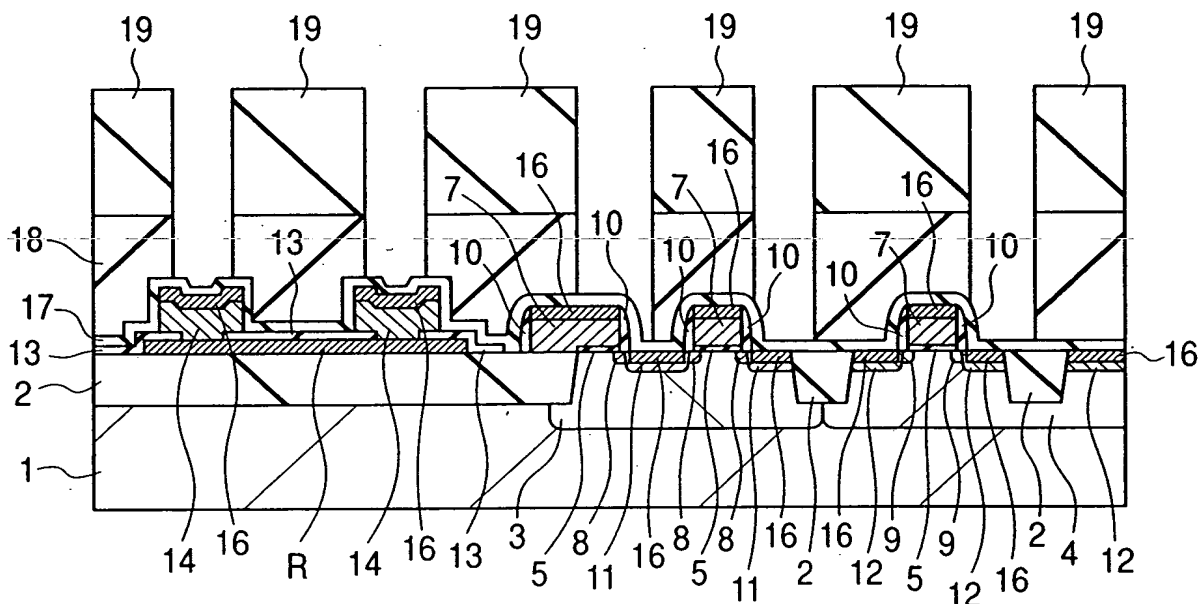


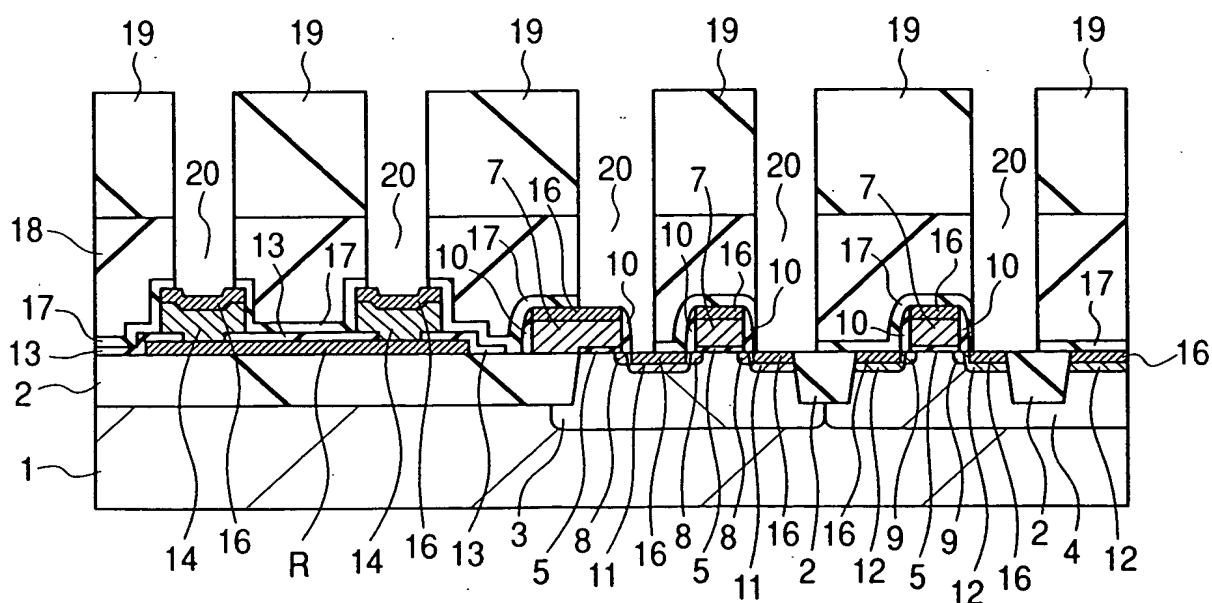
FIG. 4(b)



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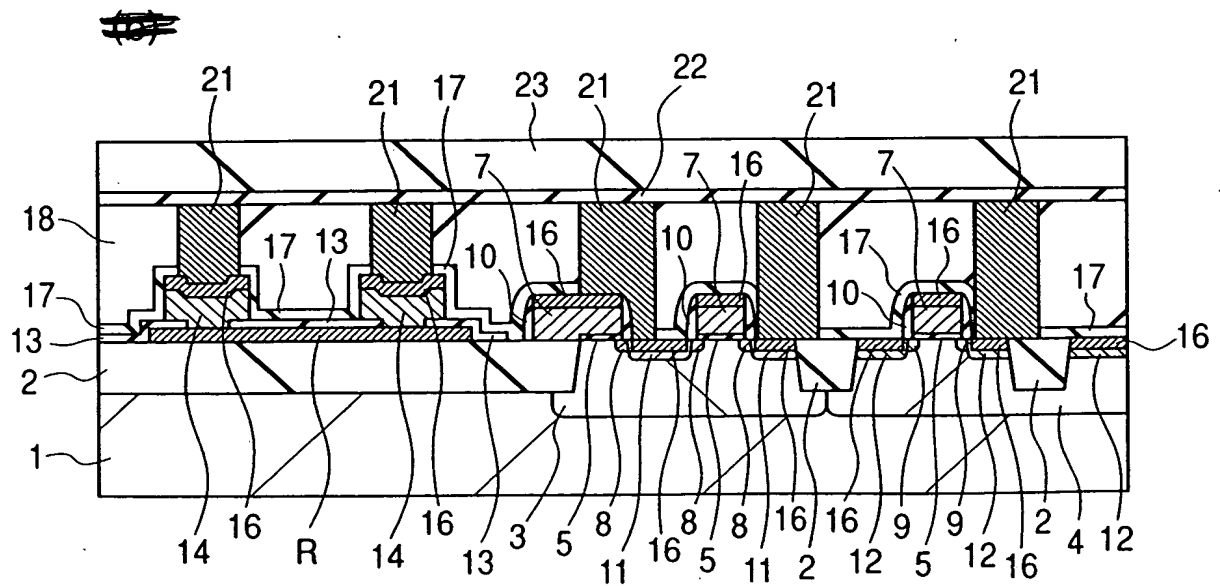
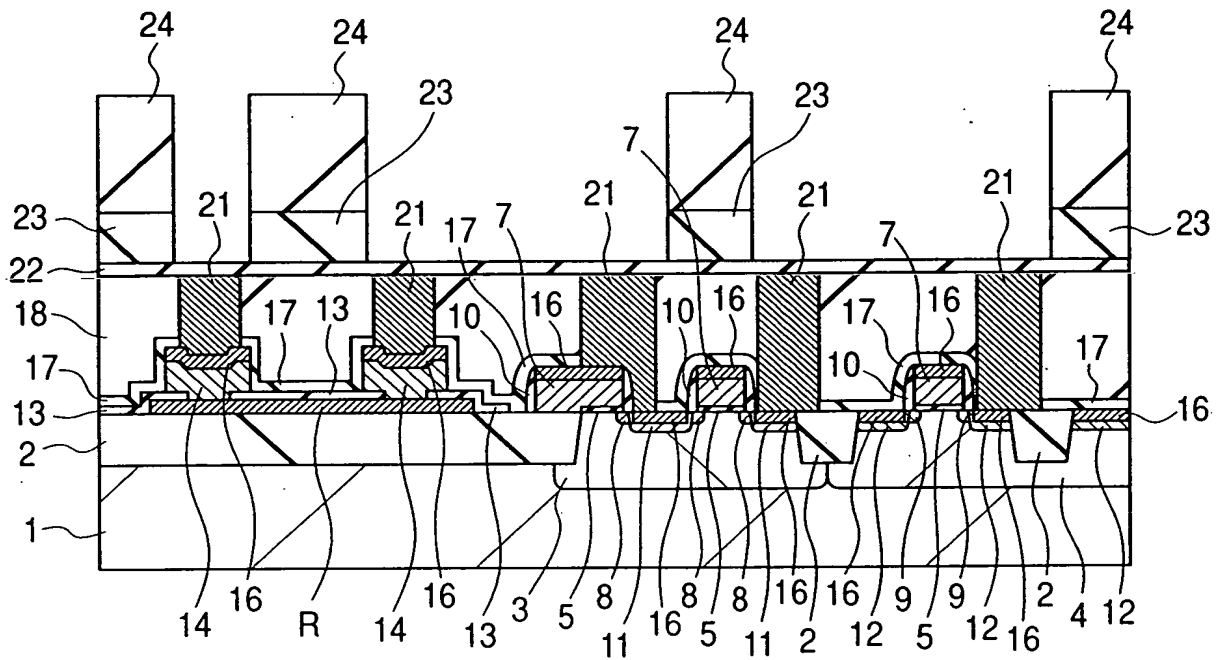


FIG. 7(a)



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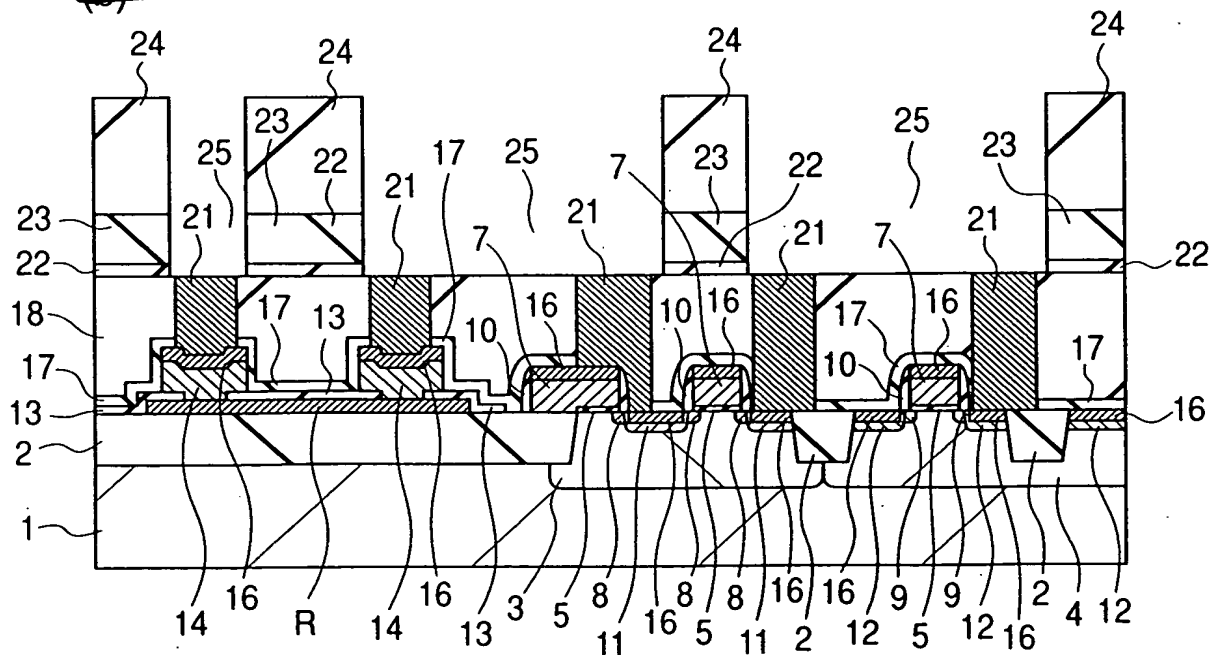


FIG. 8(a)

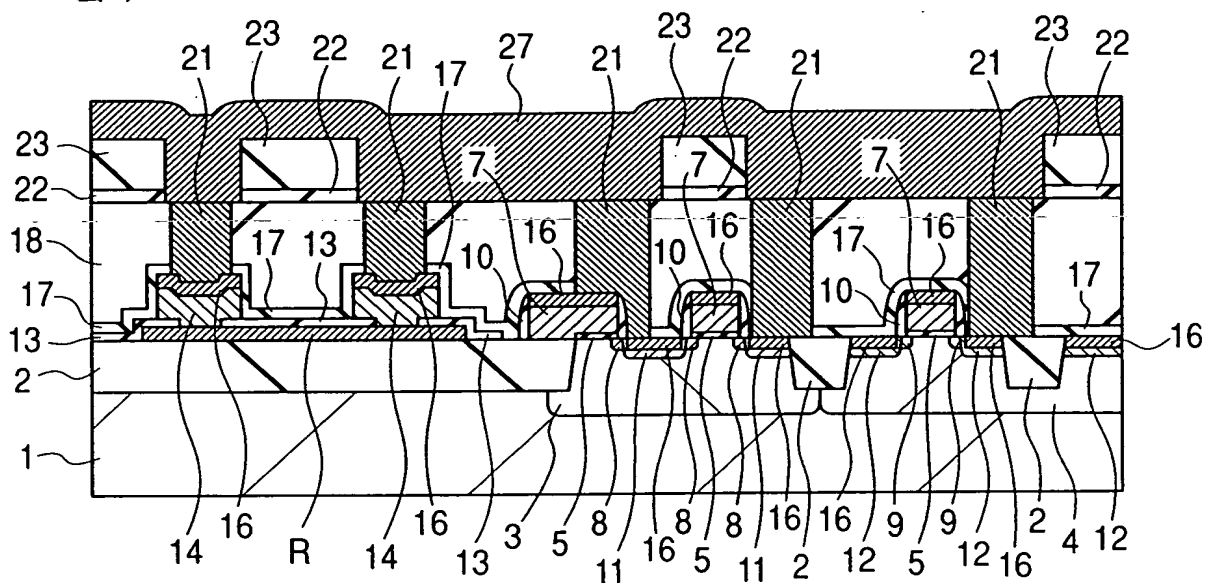


FIG. 8(b)

